

## ABSTRACT OF THE DISCLOSURE

A substrate treating method and apparatus are disclosed, which are capable of treating substrates having a material of high dielectric constant, reliably at a relatively low temperature. A treating solution containing sulfuric acid ( $H_2SO_4$ ) and hydrofluoric acid (HF) or sulfuric acid ( $H_2SO_4$ ) and buffered hydrofluoric acid ( $NH_4F \cdot HF$ ) is used for treating substrates coated with a film including the material of high dielectric constant. The material of high dielectric constant may be treated selectively by the treating solution at the relatively low temperature.